

184-P065D1C1

PATENT

APPLICATION DATA SHEET

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Application Information: Title: METHOD AND SYSTEM FOR REDUCING SHORT
 CHANNEL EFFECTS IN A MEMORY DEVICE BY
 REDUCTION OF DRAIN THERMAL CYCLING

Classification: Class: Subclass:
 Tech Center:
 Drawing Sheets: 6 Drawing to be Published:
 Docket No: 184-P065D1C1
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 Secrecy: None

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Domestic Priority:

Application:	Continuity Type:	Parent Application:	Parent Filing Date:
This Application	Continuation of	10/119,571	April 9, 2002
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Foreign Priority Information

Country:	Application Number:	Filing Date:	Priority Claimed:
None			

Assignee: Advanced Micro Devices, Inc.
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